

FEATURES

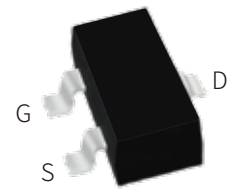
Ultra low on-resistance: $V_{DS}=30V, R_{DS(ON)} \leq 50m\Omega$

@ $V_{GS}=4.5V, I_D=3.6A$

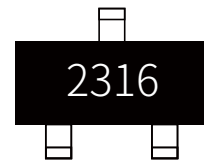
For Low power DC to DC converter application

For Load switch application

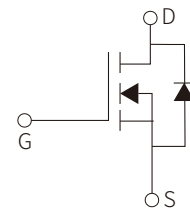
Surface Mount device



SOT-23



Marking



Schematic Symbol

APPLICATION

Case: SOT-23

Case Material: Molded Plastic. UL flammability

Classification Rating: 94V-0

APPROVALS

RoHS Compliance with 2011/65/EU

HF Compliance with IEC61249-2-21:2003

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Continuous drain current	I_D	3.6	A
Pulsed drain current (Note 1)	I_{DM}	16	A
Gate-Source Voltage	V_{GS}	± 20	V
Power dissipation	P_D	0.96	W
Thermal resistance from Junction to ambient	$R_{\theta JA}$	175	$^\circ\text{C}/\text{W}$
Junction temperature	T_J	150	$^\circ\text{C}$
Storage temperature	T_{STG}	-55 to 150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS(T_a =25°C)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =10μA	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =24V, V _{GS} =0V			1	μA
Gate-Body Leakage	I _{GSS}	V _{GS} =±20V, V _{DS} =0V			±100	nA
Gate Threshold Voltage (Note1)	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.8			V
On-State Drain Current	I _{D(on)}	V _{DS} =4.5V, V _{GS} =10V	6			A
		V _{DS} =4.5V, V _{GS} =4.5V	4			
Static Drain-Source On-Resistance(Note1)	R _{DS(on)}	V _{GS} =4.5V, I _D =3.6A		42	50	mΩ
		V _{GS} =4.5V, I _D =2.6A		68	85	
Forward Transconductance(Note1)	g _{FS}	V _{DS} =4.5V, I _D =3.4A		6		S
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, f=1.0MHz		215		pF
Output Capacitance	C _{oss}			90		
Reverse Transfer Capacitance	C _{rss}			55		
Turn-On Delay Time	t _{d(on)}	V _{GS} =10V, R _{GEN} =6Ω V _{DD} =15V, I _D =1A R _L =15Ω		9	15	ns
Turn-On Rise Time	t _r			9	15	
Turn-Off Delay Time	t _{d(off)}			14	20	
Turn-Off Fall Time	t _f			6	12	
Diode forward voltage (note 1)	V _{SD}	I _S =0.94A, V _{GS} =0V		0.88	1.2	V
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =15V, I _D =3.6A		4.3	7	nC
Gate Source Charge	Q _{gs}			0.65		
Gate Drain Charge	Q _{gd}			1.2		
Diode forward current	I _S	V _D =V _G =0V, V _S =1.2V		0.8		A

Note:1. Pulse test ; Pulse width ≤400μs, Duty cycle ≤ 2%

PARAMETER CHARACTERISTIC CURVE

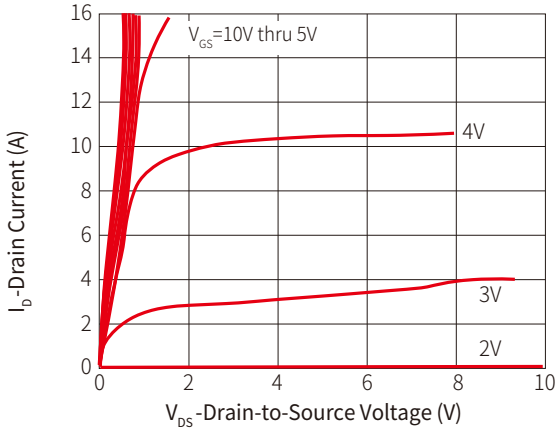
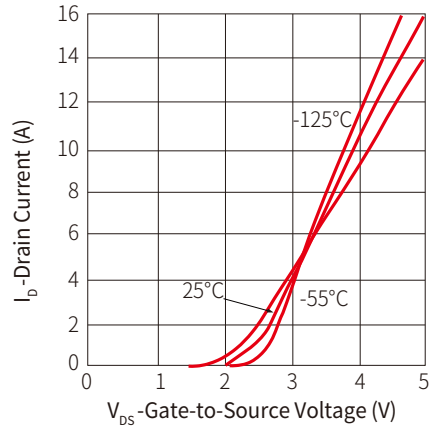
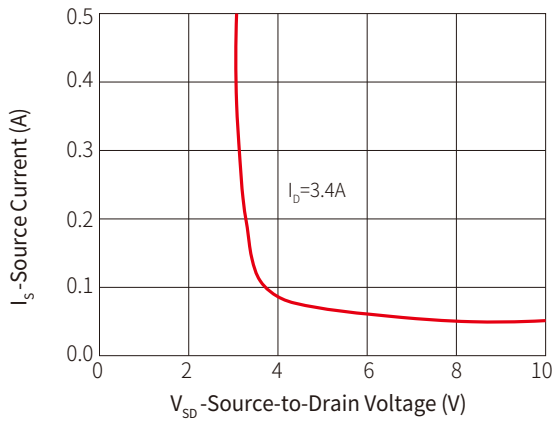
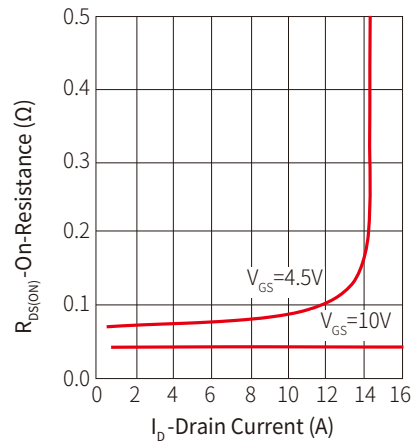
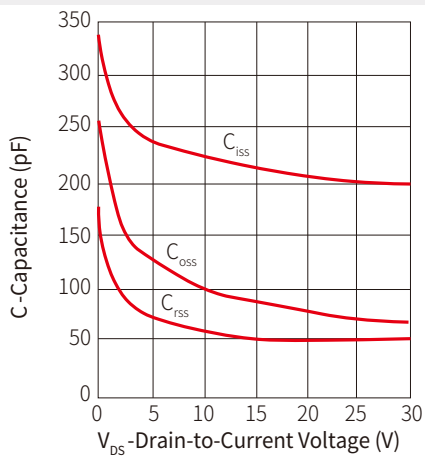
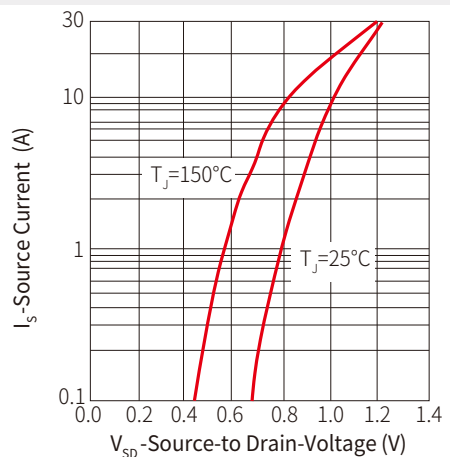
Fig 1: Typical Output Characteristics

Figure 2: Transfer Characteristics

Figure 3: On-Resistance vs. Gate-to-Source Voltage

Figure 4: On-Resistance vs. Drain Current

Figure 5: Capacitance

Figure 6: Source Diode Forward Voltage


Figure 7: Gate Charge

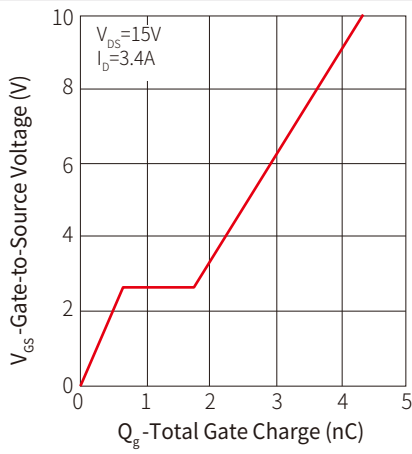


Figure 8: Single Pulse Power

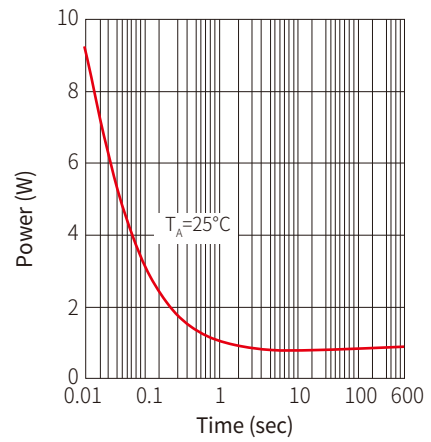
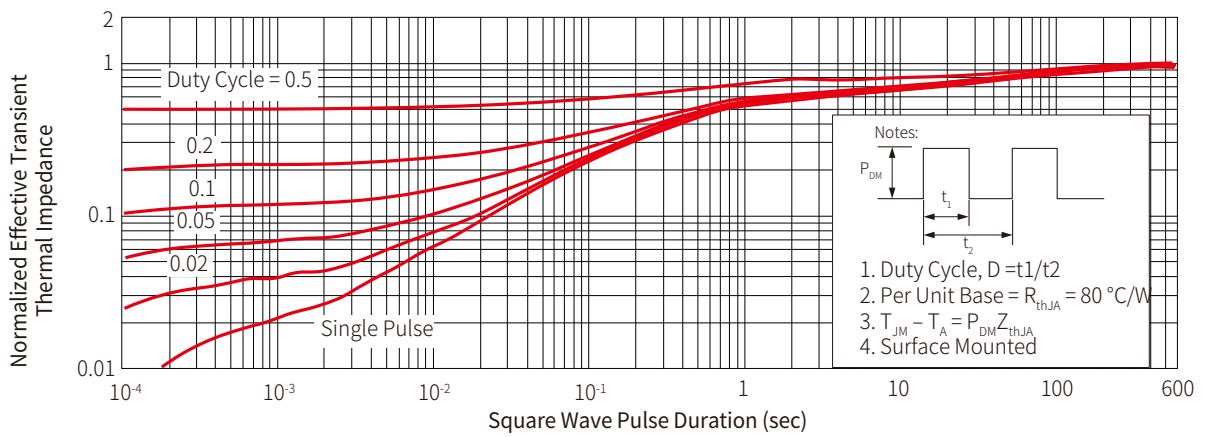
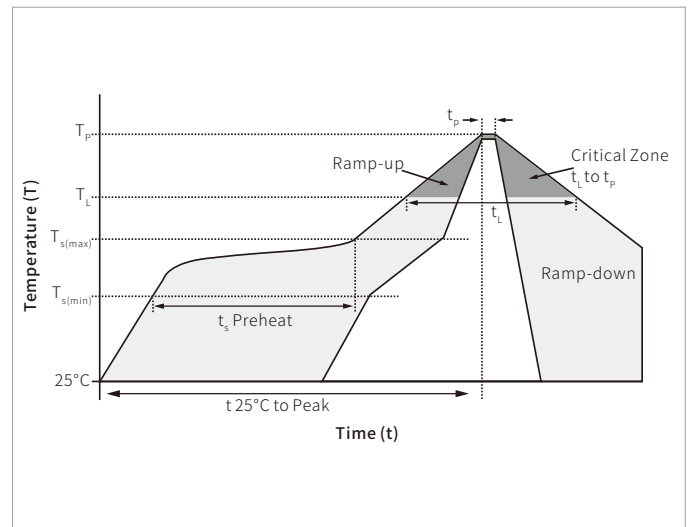


Figure 9: Normalized Thermal Transient Impedance

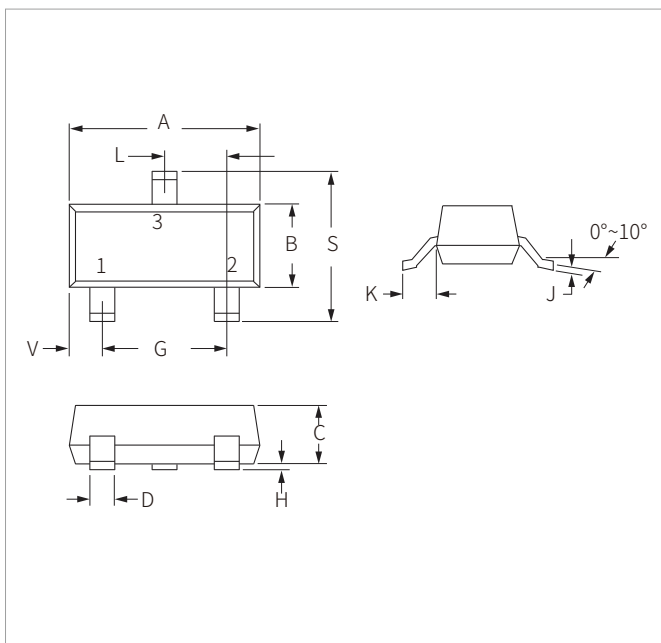


SOLDERING PARAMETERS

Reflow Condition		Lead-free assembly
Pre Heat	Temperature Max ($T_{s(min)}$)	150°C
	Temperature Max ($T_{s(max)}$)	200°C
	Time (min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus Temp (T_L) to peak)		3°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/second max
Reflow	Temperature (T_L) (Liquidus)	217°C
	Time (min to max) (t_r)	60 – 150 seconds
Peak Temperature (T_p)		260°C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		6°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes max.
Do not exceed		260°C

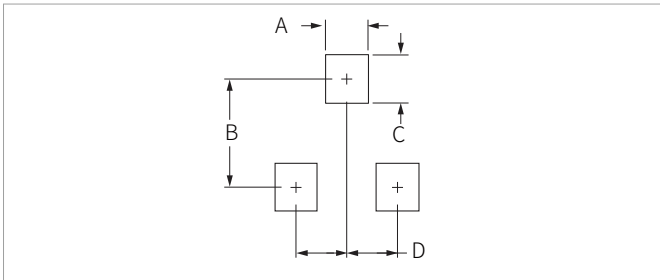


SOT-23 PACKAGE INFORMATION



Ref.	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.80	3.05	0.110	0.120
B	1.20	1.40	0.047	0.055
C	0.90	1.15	0.035	0.045
D	0.37	0.50	0.015	0.020
G	1.75	2.05	0.069	0.081
H	0.01	0.100	0.001	0.004
J	0.085	0.180	0.003	0.007
K	0.35	0.69	0.014	0.029
L	0.89	1.02	0.035	0.040
S	2.10	2.65	0.083	0.104
V	0.45	0.60	0.018	0.024

RECOMMENDED PAD LAYOUT DIMENSIONS



Ref.	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.71	0.97	0.028	0.038
B	1.88	2.13	0.074	0.084
C	0.71	0.97	0.028	0.038
D	0.81	1.07	0.032	0.042

ORDERING INFORMATION

Part Number	Component Package	QTY/Reel	Reel Size
SNM2316S	SOT-23	3000PCS	7"

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